

ABSTRACT OF THE DISCLOSURE

[0051] A semiconductor device may include a substrate and an insulating layer formed on the substrate. A fin may be formed on the insulating layer and may include a number of side surfaces and a top surface. A first gate may be formed on the insulating layer proximate to one of the number of side surfaces of the fin. A second gate and may be formed on the insulating layer separate from the first gate and proximate to another one of number of side surfaces of the fin.